

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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HSB88YP

Silicon Schottky Barrier Diode for High Speed Switching



ADE-208-932A (Z)

Rev. 1
Sep. 2000

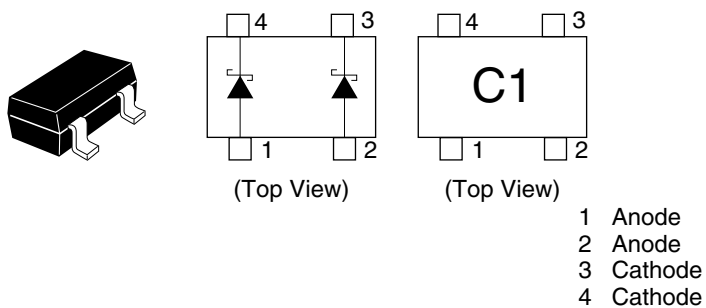
Features

- Low reverse current, Low capacitance.
- CMPAK-4 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSB88YP	C1	CMPAK-4

Pin Arrangement



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	V_R	10	V
Average rectified current	I_O^*	15	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Note: Per one device.

Electrical Characteristics *¹

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_{F1}	0.350	—	0.420	V	$I_F = 1 \text{ mA}$
	V_{F2}	0.500	—	0.580		$I_F = 10 \text{ mA}$
Reverse current	I_{R1}	—	—	0.2	μA	$V_R = 2 \text{ V}$
	I_{R2}	—	—	10		$V_R = 10 \text{ V}$
Capacitance	C	—	—	0.80	pF	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$
Capacitance deviation	ΔC	—	—	0.10	pF	$V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$
Forward voltage deviation	ΔV_F	—	—	10	mV	$I_F = 10 \text{ mA}$
ESD-Capability * ²	—	30	—	—	V	C = 200 pF, R = 0 Ω, Both forward and reverse direction 1 pulse.

Notes: 1. Per one device.

2. Failure criterion ; $I_R > 0.4 \text{ μA}$ at $V_R = 2 \text{ V}$

Main Characteristic

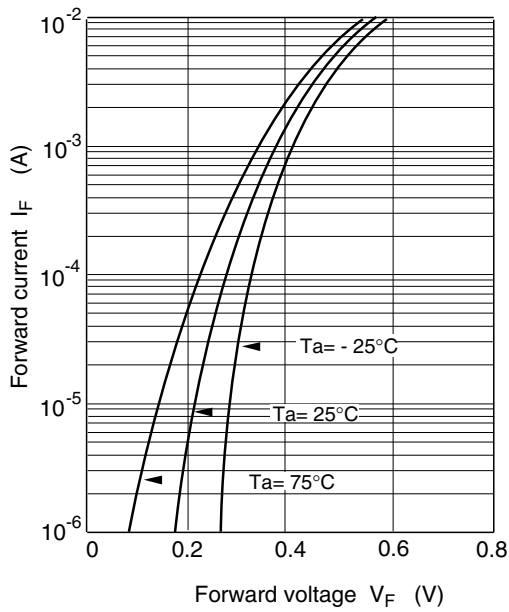


Fig.1 Forward current Vs. Forward voltage

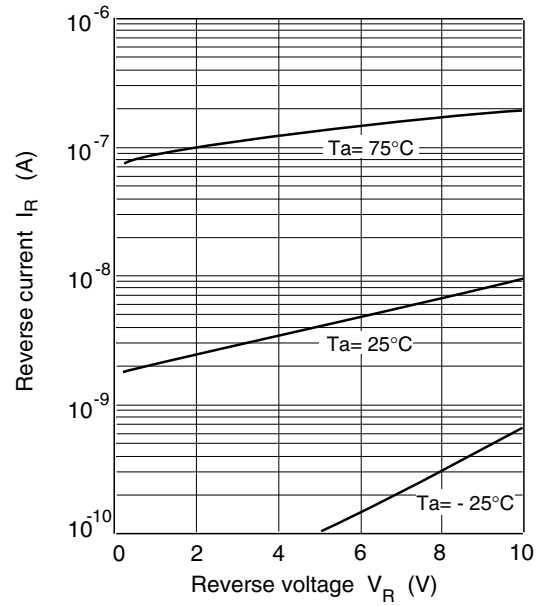


Fig.2 Reverse current Vs. Reverse voltage

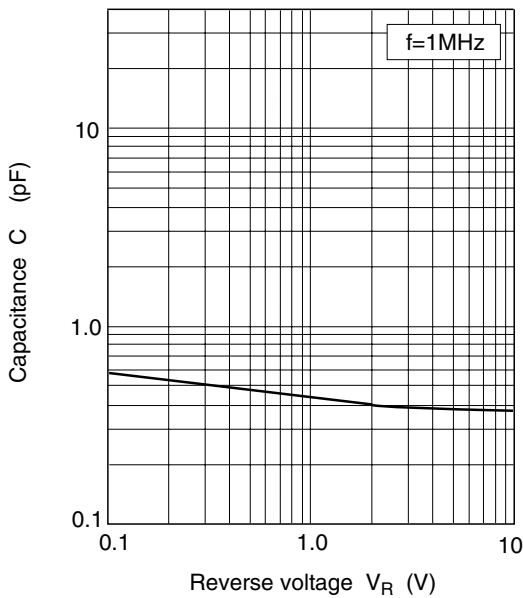
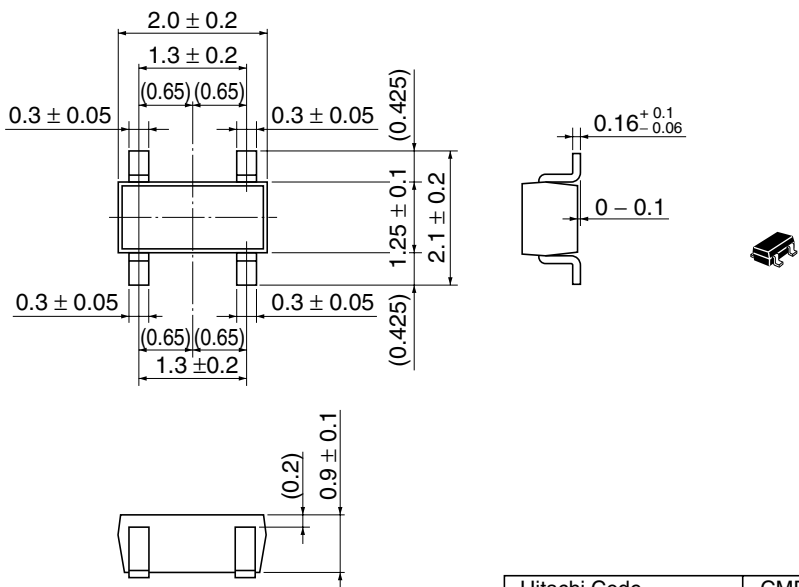


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



Hitachi Code	CMPAK-4(D)
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.006 g

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Sales Offices

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia	: http://sicapac.hitachi-asia.com
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For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe Ltd. Electronic Components Group Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 585200
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Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road
Hung-Kuo Building
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://semiconductor.hitachi.com.hk>

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